Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	28	("20020119629"|"20020142543"|"20020142545"|"20030052361"|"6077733"|"6174767"|"6225646"|"6261905"|"6435942"|"6436764"|"6436769"|"6440796"|"6441429"|"6451654"|"6451698"|"6451699"|"6455836"|"6464855"|"6465841"|"6468863"|"6479348"|"6482700"|"6486032"|"6489649"|"6492231"|"6504206"|"6524167"|"6524915"|"6528844"|"6531732"|"6531734"|"6534821").PN.	USPAT	OR	OFF	2006/01/05 13:26
L2	50	("6287765" "5739254" "5753783" "5945253" "6151042" "5551142" "6063207" "6153479" "6033968" "6242342" "6146940" "6113069" "6182633" "5389182" "4284659" "5188191" "5489079" "5607882" "4856252" "5325952" "5452401" "5563084" "5655124" "5787297" "5877034" "6137708" "5590346" "5602854" "5606347" "6002946" "5565745" "5706237" "6056869" "6057924" "4257099" "4314521" "4519371" "5618149" "5645261" "5660451" "5674774" "5725194" "5998909" "6101094" "4455660" "5187853" "5297690" "4426251" "5376571" "5813752").pn.	USPAT	OR	OFF	2006/01/05 13:29
L3	222	438/267.ccls.	USPAT	OR	OFF	2006/01/05 13:30
L4	274	438/267.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/05 13:30
S1	61	("20020119629"|"20020142543"|"20020142545"|"20030052361"|"6077733"|"6174767"|"6225646"|"6261905"|"6435942"|"6436764"|"6436769"|"6440796"|"6441429"|"6451654"|"6451698"|"6451699"|"6455836"|"6464855"|"6465841"|"6468863"|"6479348"|"6482700"|"6486032"|"6489649"|"6492231"|"6504206"|"6524167"|"6524915"|"6528844"|"6531732"|"6531734"|"6534821").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/13 20:03

S2	6	flash and SGFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 19:43
S3	2	"6855602".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/13 20:10
S4	2	"6136710".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/13 20:10
S5	2	("20030129840" | "20040036118").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/09/13 20:13
S6	1	("6855602").URPN.	USPAT	OR	OFF	2005/09/13 20:14
S7	56671	memory adj device and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 19:44
S8	3968	memory adj device and transistor and second adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 19:49
S9	2	Partially near2 memory adj device and Partially near2 transistor same first adj layer and second adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 19:58
S10	2	Partially near2 memory adj device and transistor same first adj layer and second adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 19:58
S11	938	memory adj device and transistor same first adj layer and second adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/15 19:58
S12	5	("5989960" | "6143609" | "6248633" | "6255205" | "6258668").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/01/05 10:37
S13	5	("6524915").URPN.	USPAT	OR	OFF	2006/01/05 10:45
S14	1	"6855602".pn.	USPAT	OR	OFF	2006/01/05 10:46
S15	1	"6136710".pn.	USPAT	OR	OFF	2006/01/05 13:19